

# **SWITCHMODE** <sup>™</sup> **Series NPN Silicon Power Transistors**

These transistors are designed for high–voltage, high–speed, power switching in inductive circuits where fall time is critical. They are particularly suited for line–operated switchmode applications. The MJ16022 is a selected high–gain version of the MJ16020 for applications where drive current is limited.

#### Features:

• Fast Switching Times:

30 ns (Typ) Inductive Fall Time 50 ns (Typ) Inductive Crossover Time 800 ns (Typ) Inductive Storage Time

• 100°C Performance Specified for:

Reverse–Biased SOA with Inductive Loads Switching Times with Inductive Loads Saturation Voltages

## **Typical Applications:**

- Switching Regulators
- Inverters
- Solenoids and Relay Drivers
- Motor Controls
- Deflection Circuits

## **MAXIMUM RATINGS** (T<sub>C</sub> = 25°C unless otherwise noted)

Rating	Symbol	Max	Unit
Collector–Emitter Sustaining Voltage	V <sub>CEO</sub>	450	Vdc
Collector–Emitter Breakdown Voltage	V <sub>CEV</sub>	850	Vdc
Emitter–Base Voltage	V <sub>EB</sub>	6	Vdc
Collector Current — Continuous — Peak (1)	I <sub>C</sub>	30 40	Adc
Base Current — Continuous — Peak (1)	I <sub>B</sub> I <sub>BM</sub>	20 30	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	P <sub>D</sub>	250 1.42	Watts W/°C
Operating and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-65 to 200	°C

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance — Junction to Case	$R_{ heta JC}$	0.7	°C/W
Maximum Lead Temperature for Soldering Purposes: 1/8" from Case for 5 Seconds	TL	275	°C

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## MJ16020 MJ16022

NPN SILICON POWER TRANSISTOR 30 AMPERES 450 VOLTS



CASE 197A-05 TO-204AE

<sup>(1)</sup> Pulse Test: Pulse Width = 5 ms, Duty Cycle < 10%.

## MJ16020 MJ16022

## **ELECTRICAL CHARACTERISTICS** ( $T_C = 25$ °C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS*			•	•	•	
Collector–Emitter Sustaining Voltage (I <sub>C</sub> = 1 mA, I = 0)		V <sub>CEO(sus)</sub>	450	_	_	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 850 Vdc, R <sub>BE</sub> = 50 Ohms, T <sub>C</sub> = 100°C)		I <sub>CER</sub>	_	_	_	mAdc
Collector Cutoff Current $(V_{CE} = 850 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc})$ $(V_{CE} = 850 \text{ Vdc}, V_{EB(off)} = 1.5 \text{ Vdc})$	@ T <sub>C</sub> = 25°C @ T <sub>C</sub> = 100°C	I <sub>CES</sub>	_	_	0.5 5	nAdc
Emitter Cutoff Current $(V_{EB} = 6 \text{ Vdc}, I_C = 0)$		I <sub>EBO</sub>	_	_	2	nAdc
ON CHARACTERISTICS*						
Base–Emitter Saturation Voltage ( $I_C = 20$ Adc, $I_B = 2$ Adc) ( $I_C = 20$ Adc, $I_B = 2$ Adc)	@ T <sub>C</sub> = 100°C	V <sub>BE(sat)</sub>	_		1.5 1.5	Vdc
Collector–Emitter Saturation Voltage ( $I_C = 20$ Adc, $I_B = 1.4$ Adc) ( $I_C = 20$ Adc, $I_B = 2.6$ Adc) ( $I_C = 20$ Adc, $I_B = 2.6$ Adc)	@ T <sub>C</sub> = 25°C @ T <sub>C</sub> = 25°C @ T <sub>C</sub> = 100°C	V <sub>CE(sat)</sub>	_ _ _	_ _ _	2.5 3 3	Vdc
DC Current Gain (I <sub>C</sub> = 30 Adc, V <sub>CE</sub> = 5 Vdc)	MJ16020 MJ16022	h <sub>FE</sub>	5 7	_ _		_
DYNAMIC CHARACTERISTICS		_	-		-	
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f <sub>test</sub> = 1 MHz)		C <sub>ob</sub>	_		800	pF

<sup>\*</sup>Indicates Pulse Test: Pulse Width = 300 µs Max, Duty Cycle = 2%.

## MJ16020 MJ16022

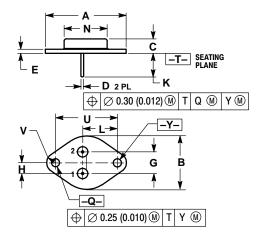
## **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

	Characteristic			Min	Тур	Max	Unit
SWITCHING CHARA	ACTERISTICS: MJ16020		•				•
Resistive Load							
Delay Time			t <sub>d</sub>	_	20	_	ns
Rise Time	- (V <sub>CC</sub> = 250 Vdc,	$I_{B2} = 5.2 \text{ Adc}$	t <sub>r</sub>	_	200	_	
Storage Time	$I_C = 20 \text{ Adc},$	$R_B = 1.6 \text{ Ohm}$ $t_s$	_	1200	_		
Fall Time	$I_{B1} = 2.6 \text{ Adc},$ $t_{D} = 30  \mu\text{s},$		t <sub>f</sub>	_	200	_	
Storage Time	Duty Cycle < 2%)	0/ 5//42	t <sub>s</sub>	_	650	_	
Fall Time		$(V_{BE(off)} = 5 \text{ Vdc})$	t <sub>f</sub>	_	80	_	
Inductive Load			•				•
Storage Time	(I <sub>C</sub> = 20 A, I <sub>B1</sub> = 2.6 Adc,		t <sub>sv</sub>	_	800	2000	ns
Crossover Time	$V_{CE(pk)} = 400 \text{ V},$	(T <sub>C</sub> = 100°C)	t <sub>fi</sub>	_	50	200	
Fall Time	$V_{BE(off)} = 5 \text{ Vdc}$		t <sub>c</sub>	_	90	250	
Storage Time	(I <sub>C</sub> = 20 A, I <sub>B1</sub> = 2.6 Adc,		t <sub>sv</sub>	_	1050	_	
Crossover Time	$V_{CE(pk)} = 400 \text{ V}, V_{BE(off)} = 5 \text{ Vdc}$	(T <sub>C</sub> = 150°C)	t <sub>fi</sub>	_	70	_	
Fall Time			t <sub>c</sub>	_	120	_	
SWITCHING CHARA	ACTERISTICS: MJ16022		•				
Resistive Load							
Delay Time			t <sub>d</sub>	_	20	_	ns
Rise Time	(V <sub>CC</sub> = 250 Vdc,	$I_{B2} = 5.2 \text{ Adc}$	= 5.2 Adc	200	_		
Storage Time	I <sub>C</sub> = 20 Adc,	R <sub>B</sub> = 1.6 Ohm	t <sub>s</sub>	_	900	_	
Fall Time	$I_{B1} = 2.6 \text{ Adc},$ $t_p = 30  \mu \text{s},$		t <sub>f</sub>	_	150	_	
Storage Time	Duty Cycle < 2%)	() (140)	t <sub>s</sub>	_	500	_	
Fall Time		$(V_{BE(off)} = 5 \text{ Vdc})$	t <sub>f</sub>	_	40	_	
Inductive Load							
Storage Time	(I <sub>C</sub> = 20 A, I <sub>B1</sub> = 2.6 Adc,		t <sub>sv</sub>	_	650	1700	50
Crossover Time	$V_{CE(pk)} = 400 \text{ V},$ $V_{BE(off)} = 5 \text{ Vdc})$	(T <sub>C</sub> = 100°C)	t <sub>fi</sub>	_	30	150	
Fall Time			t <sub>c</sub>	_	50	200	
Storage Time	(I <sub>C</sub> = 20 A, I <sub>B1</sub> = 2.6 Adc, V <sub>CE(pk)</sub> = 400 V, V <sub>BE(off)</sub> = 5 Vdc)		t <sub>sv</sub>	_	850	_	
Crossover Time		(T <sub>C</sub> = 150°C)	t <sub>fi</sub>	_	30	_	
Fall Time			t <sub>c</sub>	_	70	_	

#### MJ16020 MJ16022

#### PACKAGE DIMENSIONS

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#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS			
DIM	MIN	MAX	MIN	MAX		
Α	1.530 REF		38.86 REF			
В	0.990	1.050	25.15	26.67		
C	0.250	0.335	6.35	8.51		
D	0.057	0.063	1.45	1.60		
E	0.060	0.070	1.53	1.77		
G	0.430 BSC		10.92 BSC			
Н	0.215 BSC		5.46	5.46 BSC		
K	0.440	0.480	11.18	12.19		
L	0.665	0.665 BSC		16.89 BSC		
N	0.760	0.830	19.31	21.08		
Q	0.151	0.165	3.84	4.19		
U	1.187 BSC		30.15	BSC		
٧	0.131	0.188	3.33	4.77		

STYLE 1:
PIN 1. BASE
2. EMITTER
CASE: COLLECTOR

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